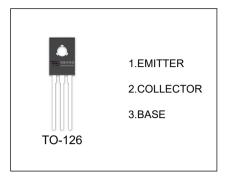


MJE170 TRANSISTOR (PNP)

FEATURES

- Low Power Audio Amplifier
- Low Current, High Speed Switching Applications



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
MJE170	TO-126	Bulk	200pcs/Bag
MJE170-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	-60	V	
V _{CEO}	Collector-Emitter Voltage	-40	V	
V _{EBO}	Emitter-Base Voltage	-7	V	
Ic	Collector Current	-3	А	
Pc	Collector Power Dissipation	1.5	W	
R _{θJA}	Thermal Resistance From Junction To Ambient	Resistance From Junction To Ambient 83		
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃	



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA,I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I_E =-1mA, I_C =0	-7			V
Collector cut-off current	I _{CBO}	V_{CB} =-60V, I_{E} =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-7V,I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	50		250	
	h _{FE(2)}	V _{CE} =-1V, I _C =-500mA	30			
	h _{FE(3)}	V _{CE} =-1V, I _C =-1.5A	12			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA,I _B =-50mA			-0.3	V
		I _C =-3A,I _B =-600mA			-1.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-1.5A,I _B =-150mA			-1.5	V
		I _C =-3A,I _B =-600mA			-2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-500mA			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0, f=10MHz			50	pF
Transition frequency	f _T	V _{CE} =-10V,I _C =-100mA, f=10MHz	50			MHz



